

**Features:**

- Pass Band : 2.6G~ 4.0 GHz
- Insertion Loss : 3.0dB
- Size : 7.67x11.0x0.5mm

**Absolute Maximum Ratings**

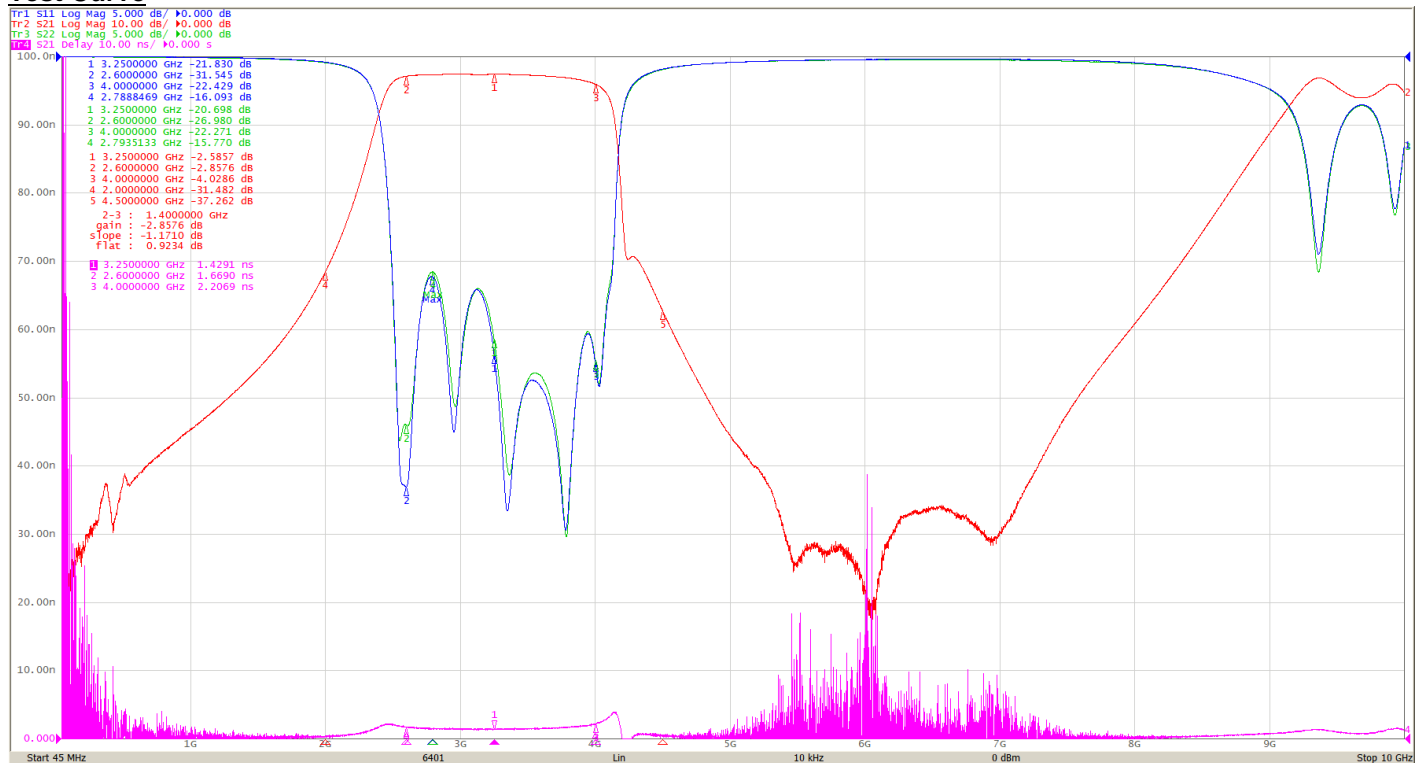
- Max. Input Power : +35dBm
- Storage Temperature : -55 ~ +85Deg.C
- Operating Temperature : -55 ~ +125Deg.C



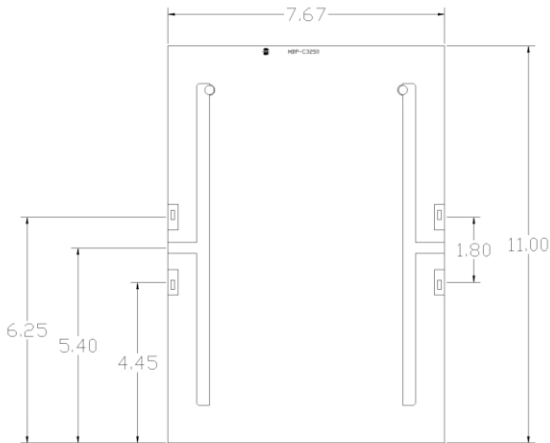
**Electrical Specifications (TA=+25Deg.C, 50Ω system)**

Parameter	Min.Value	Typical Value	Max.Value	Unit	
Frequency Range	2.6 ~ 4.0			GHz	
Insertion Loss (Fc)	-	2.58	3.0	dB	
Ripple	-	0.92	1.3	dB	
Attenuation	DC~@2GHz	30.0	31.48	-	dB
	@4.5GHz ~ 8GHz	30.0	37.26	-	dB
Return Loss	15.0	15.77	-	dB	
Group Delay	-	2.20	4.0	ns	

**Test Curve**



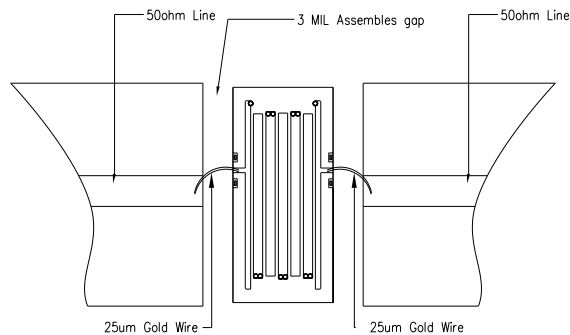
**Size**



Remarks: Unit : mm, Tolerance :  $\pm 0.25$ mm  
 1. Chip bottom is gold plated and grounded.  
 2. Bonding pressure points are gold plated.  
 3. Don't bond on the through holes.

**Applications**

1. Assembly and Bonding Diagram. (Reference)



Assembly Diagram

2. The chip is back-metalized and can be die mounted with AuSn eutectic performs or with electrically conductive epoxy (for example ME8456).
3. The die should be assembled on carriers like Kovar or Mu-Cu which have same Coefficient of thermal expansion. (2.9ppm/°C) with Silicon, thickness 0.2mm max.
4. Handle the chips in a clean environment. DO NOT attempt to clean the chip using liquid cleaning systems.
5. Handle the chip along the edges with a vacuum collet or with a sharp pair of bent tweezers.